

ABSTRACT OF THE DISCLOSURE

A new dielectric material composition with high dielectric constant and low dielectric loss, which includes a quaternary metallic oxide having a perovskite structure and
5 represented by a general formula, $Ba_{1-x}M^1_xTi_{1-y}M^2_yO_m$. It is suitable for Gbit memory devices, embedded capacitance devices in multilayered structures, and modulable capacitors for high frequency devices.